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PATENT
Customer No. 22,852
Attorney Docket No. 04329.2613

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Katsuhiko HIEDA

Serial No.: 09/916,509

Filed: July 30, 2001

For: SEMICONDUCTOR DEVICE AND
METHOD FOR MANUFACTURING
THE SAME

Group Art Unit: 2814

Examiner: T. Le

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Commissioner for Patents
Washington, DC 20231

Sir:

TRANSMITTAL LETTER

Enclosed is a reply to the Office Action of March 11, 2002. The items checked below are appropriate:

- ☐ Applicant hereby petitions for a month extension of time to respond to the above Office Action. The fee of \$ for the Extension is enclosed.

The claims are calculated below:

	Claims Remaining After Amendment		Highest Number Previously Paid	Present Extra	Rate	Additional Fee
Total	45	-	43	2	x \$ 18	\$ 36.00
Indep.	19	-	19	0	x \$ 84	0.00
<input type="checkbox"/> First Presentation of Multiple Dep. Claim(s)					+\$280	0.00
Subtotal						\$ 36.00
Reduction by 1/2 if small entity						- 0.00
TOTAL						\$ 36.00

- ☒ A fee of \$36 to cover the cost of the additional claims added by this reply is enclosed.
- ☐ A fee of \$ to cover is enclosed.
- ☒ A check for \$36 to cover the above fee is enclosed.

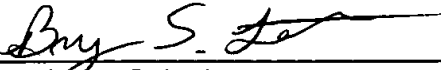


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Please grant any extensions of time required to enter this response and charge any additional required fees to our deposit account 06-0916.

Dated: April 11, 2002

By: 
Bryan S. Latham
Reg. No. 49,085

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Assistant Commissioner for Patents
Washington, DC 20231

Sir:

04/12/2002 MGBREM1 00000036 09916509

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**AMENDMENT AND RESPONSE TO
ELECTION REQUIREMENT**

Please amend the application as follows:

IN THE CLAIMS:

Please amend claim 20 and add new claims 44 and 45 as follows:

20. (Amended) The method according to claim 19, wherein the convex semiconductor layer is formed with the epitaxial growth method.

--44. (New) The device according to claim 1, wherein a position of a deepest portion of the gate electrode is deeper than a position of a deepest portion of the source region and a position of a deepest portion of the drain region.

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